AMENDMENTS TO THE CLAIMS:

The following listing of claims replaces all prior listings, and all prior versions, of claims in the application.

LISTING OF CLAIMS:

1. (Currently amended) An anodic bonding method comprising the steps of:

forming a soft metal layer on a surface of a conductor layer or a semiconductor layer;

forming an active metal layer on the soft metal layer, the active metal layer having a higher activity with oxygen than the soft metal layer; and

heating the active metal layer and the glass layer that are brought into contact with each other while applying a DC voltage, using the conductor layer or the semiconductor layer as an anode and the glass layer as a cathode, between the anode and the cathode, thereby bonding the glass layer to the conductor layer or the semiconductor layer,

wherein a metal layer comprising at least one of Al, Ti, Cr, V. and W is formed between the conductor layer or the semiconductor layer and the soft metal layer in order to improve adhesion therebetween, and a metal film comprising at least one of Cu, Ni, Pt, Pd, Ti, and Cr is formed between the soft metal layer and the active metal layer in order to prevent diffusion and reaction therebetween.

2. (Original) An anodic bonding method according to claim 1, wherein a pure metal film of Au, Ag, Cu, Ni, Pt, Pd, Pb, or Sn, or a stacked film of a plurality of the pure metals, or an alloy film thereof is used as the soft metal layer.

3. (Original) An anodic bonding method according to claim 1, wherein a pure metal film comprising at least one of Al, Cr, Ti, V, and W, or an alloy film containing at least one of the pure metals is used as the active metal film.

4. (Cancelled).

5. (Original) An anodic bonding method according to claim 1, wherein a bonded face of the glass layer is roughened.

6. (Original) An anodic bonding method according to claim 1, wherein a Si layer is used as the conductor layer or the semiconductor layer.

7. – 14. (Cancelled).